

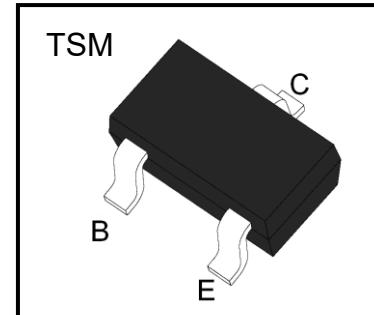
## NPN Plastic-Encapsulate Transistors

### Application

- DC-DC converter
- Relay drivers, Lamp drivers
- Motor drivers, Strobes application

### Features

- High current capacitance.
- Low collector-emitter saturation voltage.
- High speed Switching.
- High allowable power dissipation.
- Complementary to FTA1552X.



Marking: HL

### Absolute Maximum Ratings ( $T_a=25^\circ\text{C}$ )

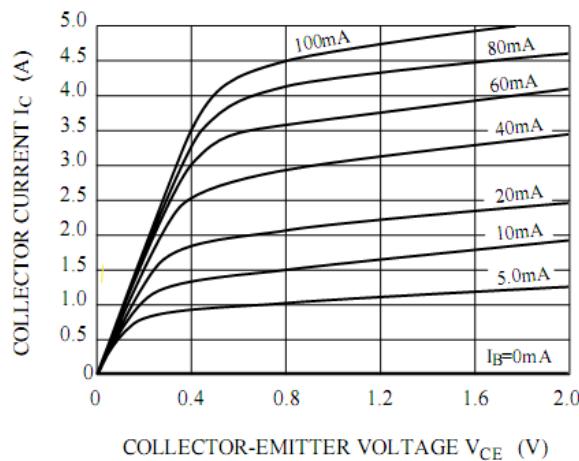
Parameter	Symbol	Value	Unit
Collector-base voltage	$\text{BV}_{\text{CBO}}$	80	V
Collector-emitter voltage	$\text{BV}_{\text{CES}}$	80	V
	$\text{BV}_{\text{CEO}}$	50	
Emitter-base voltage	$\text{BV}_{\text{EBO}}$	6	V
Collector current DC	$I_{\text{C}}$	3	A
Collector current pulse	$I_{\text{CP}}$	6	A
Base current	$I_{\text{B}}$	600	mA
Collector power dissipation*	$P_{\text{C}}$	1	W
Junction temperature	$T_{\text{j}}$	150	$^\circ\text{C}$
Storage temperature	$T_{\text{stg}}$	-55 ~ 150	$^\circ\text{C}$

\* Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm<sup>2</sup>

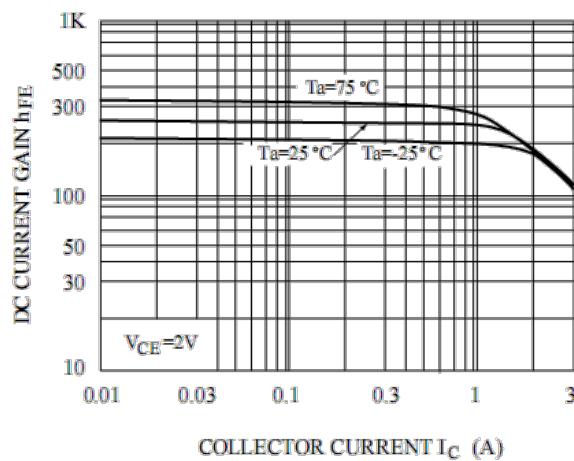
**Electrical Characteristics (Ta=25°C)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV <sub>CBO</sub>	I <sub>C</sub> = 10µA, I <sub>E</sub> = 0	80			V
Collector-emitter breakdown voltage	BV <sub>CES</sub>	I <sub>C</sub> = 100µA, V <sub>BE</sub> = 0	80			V
	BV <sub>CEO</sub>	I <sub>C</sub> = 1mA, I <sub>B</sub> = 0	50			V
Emitter-base breakdown voltage	BV <sub>EBO</sub>	I <sub>E</sub> = 10µA, I <sub>C</sub> = 0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 40V, I <sub>E</sub> = 0			0.1	µA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 4V, I <sub>C</sub> = 0			0.1	µA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 2V, I <sub>B</sub> = 100mA	200		560	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 1A, I <sub>B</sub> = 50mA			120	mV
		I <sub>C</sub> = 2A, I <sub>B</sub> = 100mA			210	
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = 2A, I <sub>B</sub> = 100mA			1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = 10V, I <sub>E</sub> = 500mA		380		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		13		pF
Turn on time	t <sub>on</sub>	V <sub>CC</sub> =25V, I <sub>C</sub> = -1A I <sub>B1</sub> = -I <sub>B2</sub> = 100mA Pw = 20µs, Duty cycle ≤ 1%		35		ns
Storage time	t <sub>stg</sub>			300		ns
Fall time	t <sub>f</sub>			22		ns

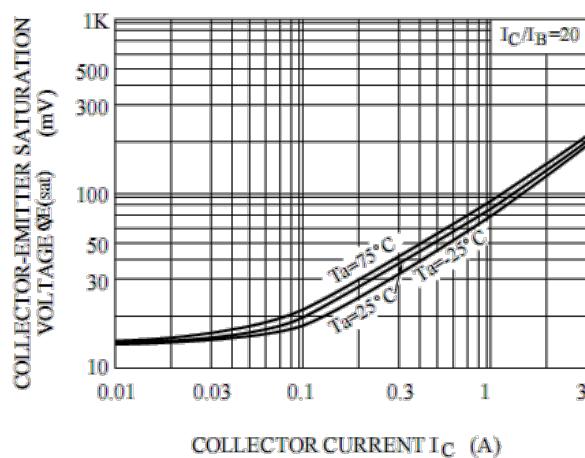
## Typical Characteristics



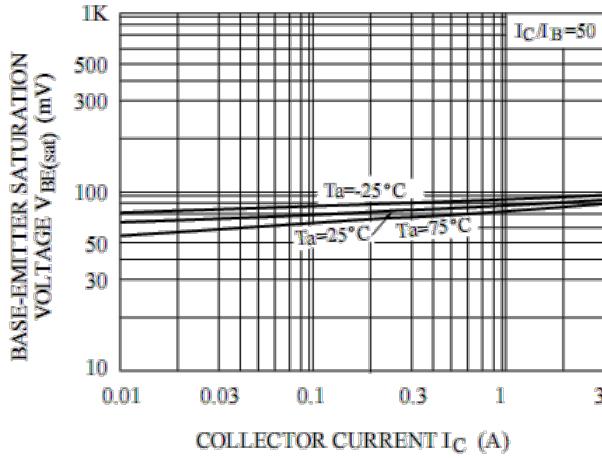
**Figure 1. Static characteristics**



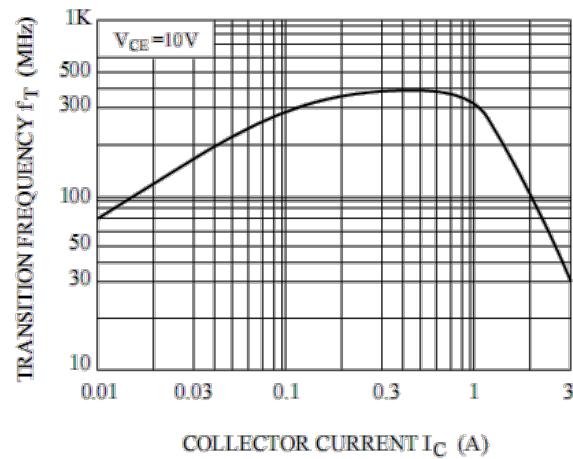
**Figure 2. DC current Gain**



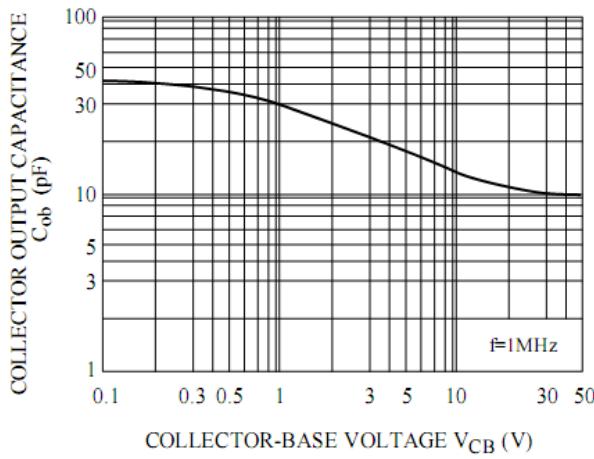
**Figure 3. Collector-emitter Saturation Voltage**



**Figure 4. Base -emitter Saturation Voltage**



**Figure 5. Transition frequency**



**Figure 6. Capacitance characteristics**

### Package Dimensions

Dim	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	1.15	1.35	0.045	0.053
A1	0.00	0.10	0.000	0.004
A2	1.05	1.25	0.041	0.049
b	0.34	0.45	0.013	0.018
c	0.10	0.20	0.004	0.008
D	2.80	3.00	0.110	0.118
E	1.50	1.70	0.059	0.067
E1	2.80	3.00	0.110	0.118
e	0.90	1.00	0.035	0.039
e1	1.80	2.00	0.071	0.079
L	0.50	0.70	0.020	0.028
L1	0.30	0.60	0.012	0.024